Power MOSFETS

DATASHEET

LM40080NAI8A

N-Channel

Enhancement Mode MOSFET

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Quality Management Systems

ISO 9001:2015 Certificate

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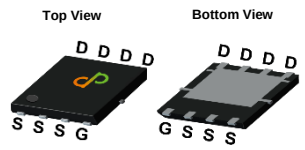
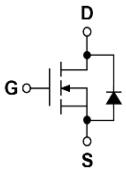
Pin Description

PDFN3.3*3.3



Symbol



Product Summary

Symbol	N-Channel	Unit
V_{DSS}	40	V
$R_{DS(ON)-Max}$	8	mΩ
ID	46	A

Feature

- Optimized technology for DC/DC Converter
- Reliable and Rugged
- ROHS Compliant & Halogen-Free
- 100% UIS and Rg Tested

Applications

- Portable Equipment
- Battery Powered System

Ordering Information

Orderable Part Number	Package Type	Form	Shipping	Marking
LM40080NAI8A	PDFN3.3*3.3	Tape & Reel	5000 / Tape & Reel	40080 □□□□□□

Note：□□□□□□ = Lot Code

Absolute Maximum Ratings (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter		N-Channel	Unit
V_{DSS}	Drain-Source Voltage		40	V
V_{GSS}	Gate-Source Voltage		±20	
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_{DM}①	Pulse Drain Current Tested	T_C=25°C	70	A
I_D	Continuous Drain Current	T_C=25°C	46	A
		T_C=100°C	29	
P_D	Maximum Power Dissipation	T_C=25°C	31	W
		T_C=100°C	13	
I_{AS}②	Avalanche Current, Single pulse	L=0.1mH	23	A
E_{AS}②	Avalanche Energy, Single pulse	L=0.1mH	26	mJ

Thermal Characteristics

Symbol	Parameter		Rating	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	Steady State	4	°C/W
$R_{\theta JA}$③	Thermal Resistance-Junction to Ambient	Steady State	60	°C/W

Note ①：Max. current is limited by bonding wire
Note ②：UIS tested and pulse width are limited by maximum junction temperature 150°C
Note ③：Surface Mounted on 1in^2 FR-4 board with 1oz.

N-Channel Electrical Characteristics (T_J=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Electrical Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250uA	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=32V, V_{GS}=0V	-	-	1	uA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250uA	1.2	1.7	2.4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V	-	-	±100	nA
$R_{DS(ON)}$④	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=20A	-	6.7	8	mΩ
		V_{GS}=4.5V, I_{DS}=15A	-	8	10	
gfs	Forward Transconductance	V_{DS}=5V, I_{DS}=5A	-	16	-	S
Dynamic Characteristics ⑤						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V, Freq.=1MHz	-	2.2	-	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=20V, Freq.=1MHz	-	1820	-	pF
C_{oss}	Output Capacitance		-	150	-	
C_{rss}	Reverse Transfer Capacitance		-	120	-	
$td_{(ON)}$	Turn-on Delay Time	V_{GS}=10V,V_{DS}=20V, I_D=1A,R_{GEN}=6Ω	-	5.8	-	nS
t_r	Turn-on Rise Time		-	22	-	
$t_{d(OFF)}$	Turn-off Delay Time		-	38	-	
t_f	Turn-off Fall Time		-	21	-	
Q_g	Total Gate Charge	V_{GS}=4.5V,V_{DS}=20V I_D=20A	-	22	-	nC
Q_g	Total Gate Charge	V_{GS}=10V,V_{DS}=20V, I_D=20A	-	44	-	
Q_{gs}	Gate-Source Charge		-	6	-	
Q_{gd}	Gate-Drain Charge		-	10	-	
Source-Drain Characteristics						
V_{SD}④	Diode Forward Voltage	I_{SD}=1A, V_{GS}=0V	-	0.7	1.1	V
t_{rr}	Reverse Recovery Time	I_F=1A, V_R=20V dI$_F$/dt=100A/μs	-	16.8	-	nS
Q_{rr}	Reverse Recovery Charge		-	8.9	-	nC

Note ④：Pulse test (pulse width≤300us, duty cycle≤2%).
Note ⑤：Guaranteed by design, not subject to production testing.

N-Channel Typical Characteristics

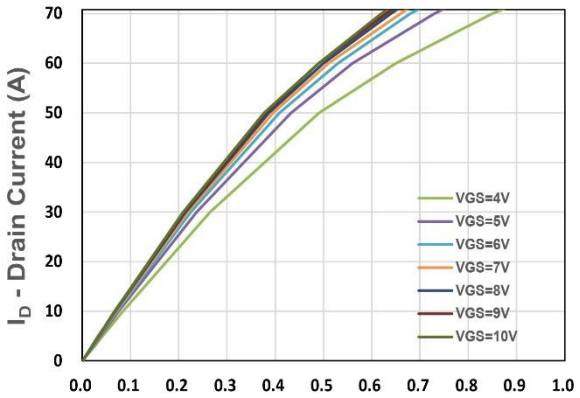


Figure 1. Output Characteristics

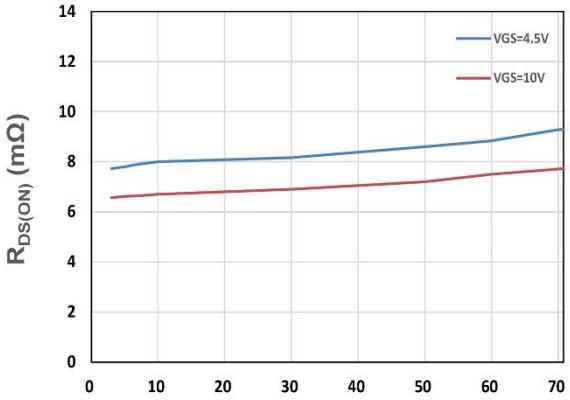


Figure 2. On-Resistance vs. ID

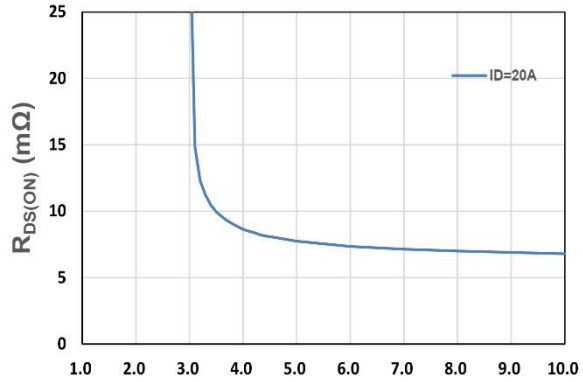


Figure 3. On-Resistance vs. VGS

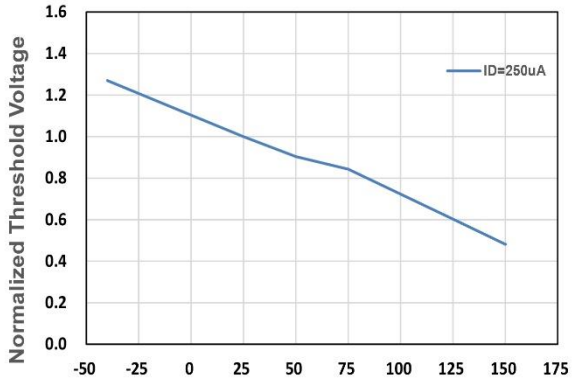


Figure 4. Gate Threshold Voltage

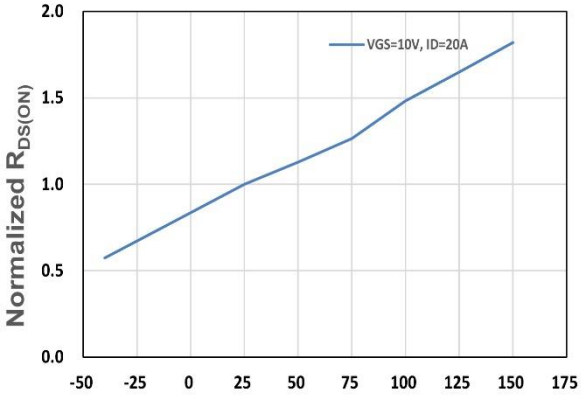


Figure 5. Drain-Source On Resistance

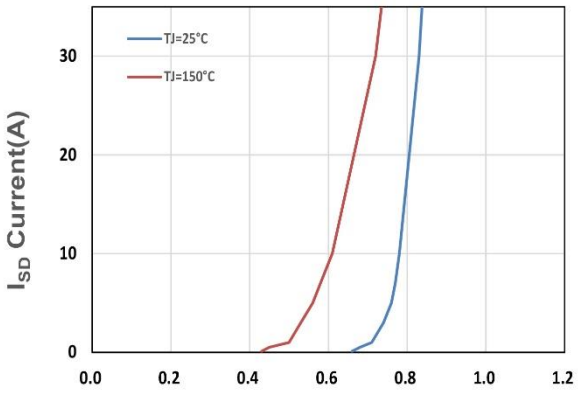


Figure 6. Source-Drain Diode Forward

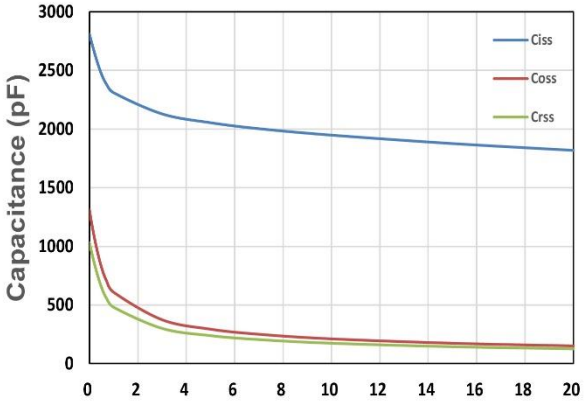


Figure 7. Capacitance

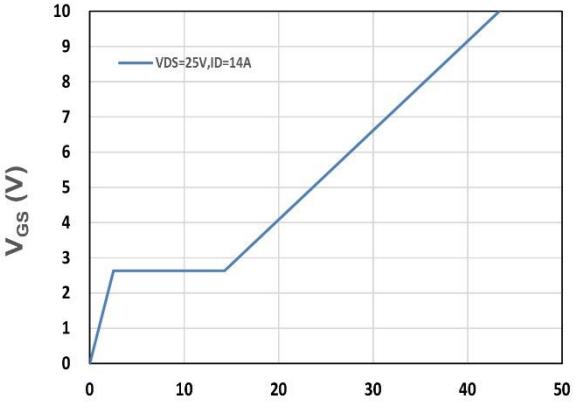


Figure 8. Gate Charge Characteristics

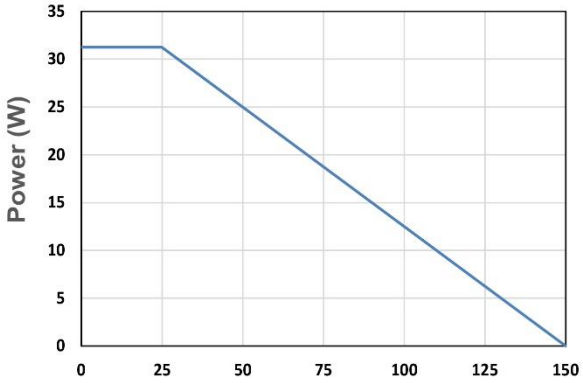


Figure 9. Power Dissipation

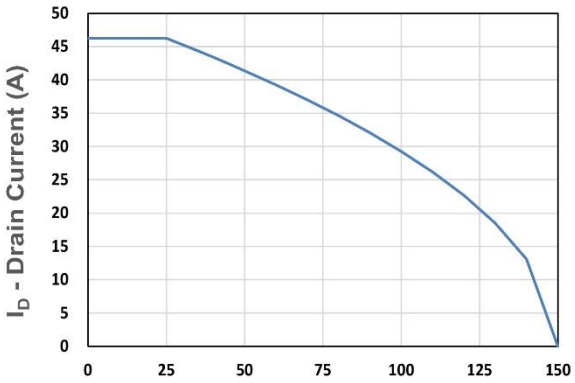


Figure 10. Drain Current

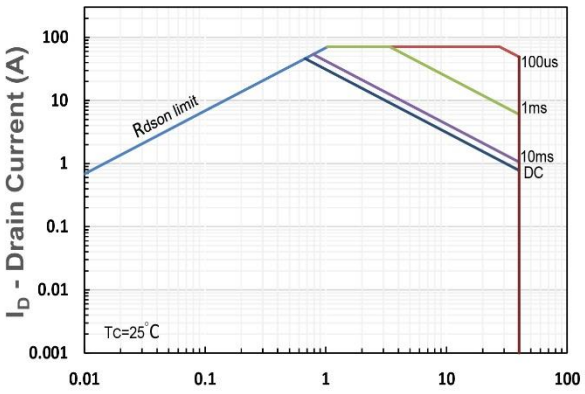


Figure 11. Safe Operating Area

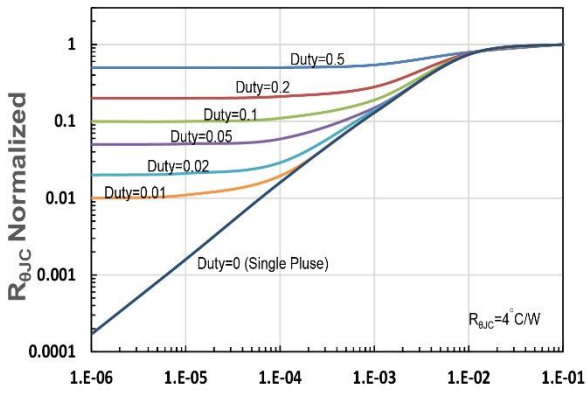


Figure 12. RθJC Transient Thermal Impedance